

GN1A - GN13

GLASS PASSIVATED JUNCTION SILICON SURFACE MOUNT

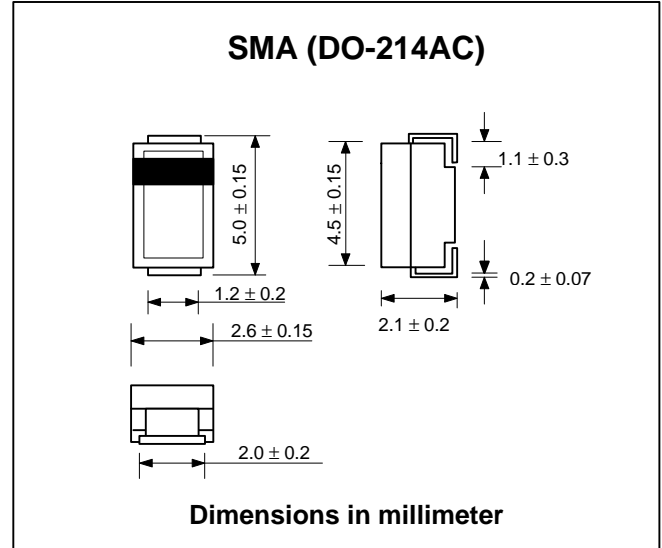
PRV : 50 - 1300 Volts
Io : 1.0 Ampere

FEATURES :

- * Glass passivated chip
- * High current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : SMA Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Lead Formed for Surface Mount
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 0.067 gram



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

RATING	SYMBOL	GN1A	GN1B	GN1D	GN1G	GN1J	GN1K	GN1M	GN13	UNIT
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	1300	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	910	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	1300	V
Maximum Average Forward Current $T_a = 75\text{ }^\circ\text{C}$	$I_{F(AV)}$	1.0								A
Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on rated load (JEDEC Method)	I_{FSM}	30								A
Maximum Forward Voltage at $I_F = 1.0\text{ Amp.}$	V_F	1.0								V
Maximum DC Reverse Current $T_a = 25\text{ }^\circ\text{C}$ at rated DC Blocking Voltage $T_a = 100\text{ }^\circ\text{C}$	I_R	5.0								μA
	$I_{R(H)}$	50								μA
Typical Junction Capacitance (Note1)	C_J	8								pF
Junction Temperature Range	T_J	- 65 to + 150								$^\circ\text{C}$
Storage Temperature Range	T_{STG}	- 65 to + 150								$^\circ\text{C}$

Notes :

(1) Measured at 1.0 MHz and applied reverse voltage of 4.0V_{DC}

RATING AND CHARACTERISTIC CURVES (GN1A - GN13)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

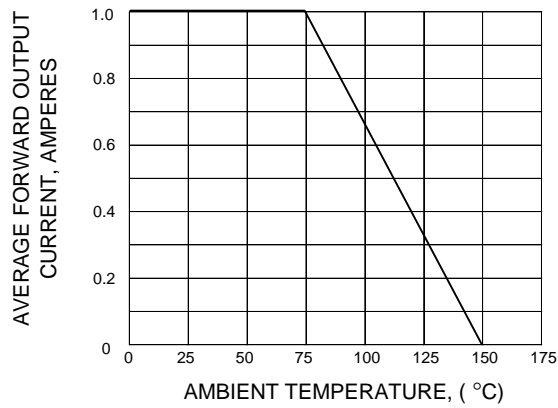


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

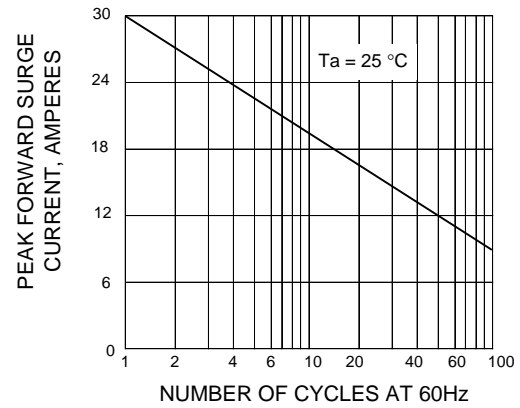


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

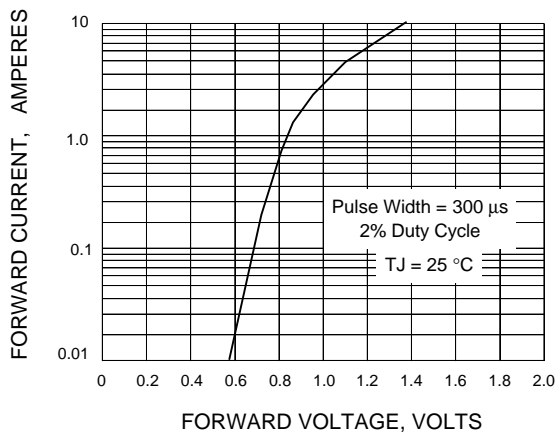


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

